

CORRECTION

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Correction: Impact of changes in bond structure on ovonic threshold switching behaviour in GeSe₂

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Correction for 'Impact of changes in bond structure on ovonic threshold switching behaviour in GeSe₂' by Jonas Keukelier *et al.*, *J. Mater. Chem. C*, 2021, DOI: 10.1039/d0tc04086j.

In the published article, Table 4 contained an error in the row "Adding Sb": the entry "Se–Se ↑" should have read "Se–Se ↓". The corrected version of Table 4 is shown below:

Table 4 Summary of the impact of several (post)deposition processes on the bond presence and electrical parameters compared to as-deposited 35% Ge GeSe₂. Arrows indicate an increased or decreased presence of bonds

Process	Impact on bonds	Impact on electrical parameters
Annealing	Pure Ge–Ge & Se–Se ↓ Ge–Se ↑	Lower I_{pris} and higher V_{FF} Leaky after FF
Increasing pressure	ETH Ge–Ge ↑ Ge–Se ↓	Higher I_{pris} and lower V_{FF} Minimal impact on V_{th}
Adding Sb	Se–Se ↓ Se–Sb & Sb–Sb ↑	Higher I_{pris} and lower V_{FF} Large variability
Adding N	Ge–Ge & Ge–Se ↓ Se–Se ↑	Lower I_{pris} and higher V_{FF} Leaky after FF
Co-doping Sb + N	Ge–Ge & Se–Se ↓ Sb–N ↑	Similar I_{pris} and lower V_{th} Better stability

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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